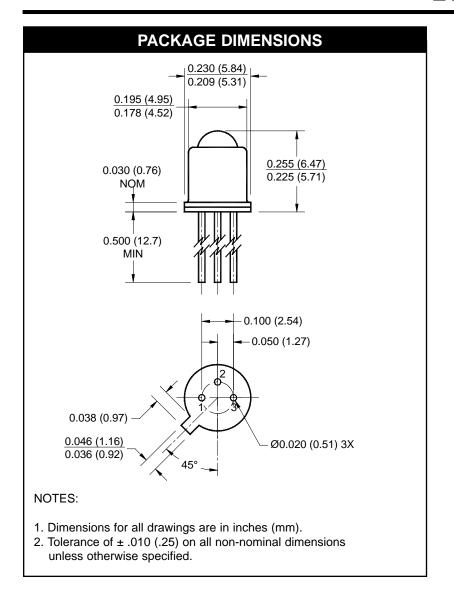
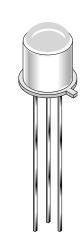
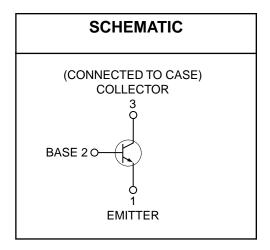
L14G1 L14G2 L14G3







#### **DESCRIPTION**

The L14G1/L14G2/L14G3 are silicon phototransistors mounted in a narrow angle, TO-18 package.

### **FEATURES**

- · Hermetically sealed package
- Narrow reception angle



L14G1 L14G2 L14G3

ABSOLUTE MAXIMUM RATINGS (T <sub>A</sub> = 25°C unless otherwise specified)								
Parameter	Symbol	Rating	Unit					
Operating Temperature	T <sub>OPR</sub>	-65 to +125	°C					
Storage Temperature	T <sub>STG</sub>	-65 to +150	°C					
Soldering Temperature (Iron)(3,4,5 and 6)	T <sub>SOL-I</sub>	240 for 5 sec	°C					
Soldering Temperature (Flow)(3,4 and 6)	T <sub>SOL-F</sub>	260 for 10 sec	°C					
Collector to Emitter Breakdown Voltage	V <sub>CEO</sub>	45	V					
Collector to Base Breakdown Voltage	V <sub>CBO</sub>	45	V					
Emitter to Base Breakdwon Voltage	V <sub>EBO</sub>	5	V					
Power Dissipation (T <sub>A</sub> = 25°C) <sup>(1)</sup>	P <sub>D</sub>	300	mW					
Power Dissipation (T <sub>C</sub> = 25°C) <sup>(2)</sup>	P <sub>D</sub>	600	mW					

#### NOTE:

- 1. Derate power dissipation linearly 3.00 mW/°C above 25°C ambient.
- 2. Derate power dissipation linearly 6.00 mW/°C above 25°C case.
- 3. RMA flux is recommended.
- 4. Methanol or isopropyl alcohols are recommended as cleaning agents.
- 5. Soldering iron tip 1/16" (1.6mm) minimum from housing.
- 6. As long as leads are not under any stress or spring tension.
- 7. Light source is a GaAs LED emitting light at a peak wavelength of 940 nm.
- 8. Figure 1 and figure 2 use light source of tungsten lamp at 2870°K color temperature. A GaAs source of 3.0 mW/cm² is approximately equivalent to a tungsten source, at 2870°K, of 10 mW/cm².

ELECTRICAL / OPTICAL CHARACTERISTICS (TA =25°C) (All measurements made under pulse conditions)								
PARAMETER	TEST CONDITIONS	SYMBOL	MIN	TYP	MAX	UNITS		
Collector-Emitter Breakdown	$I_{\rm C} = 10 \text{ mA}, Ee = 0$	BV <sub>CEO</sub>	45		_	V		
Emitter-Base Breakdown	I <sub>E</sub> = 100 μA, Ee = 0	BV <sub>EBO</sub>	5.0		_	V		
Collector-Base Breakdown	$I_{\rm C} = 100 \ \mu {\rm A, Ee} = 0$	BV <sub>CBO</sub>	45		_	V		
Collector-Emitter Leakage	V <sub>CE</sub> = 10 V, Ee = 0	I <sub>CEO</sub>	_		100	nA		
Reception Angle at 1/2 Sensitivity		θ		±10		Degrees		
On-State Collector Current L14G1	Ee = 0.5 mW/cm <sup>2</sup> , $V_{CE} = 5 V^{(7,8)}$	I <sub>C(ON)</sub>	1.0		_	mA		
On-State Collector Current L14G2	Ee = 0.5 mW/cm <sup>2</sup> , $V_{CE} = 5 V^{(7,8)}$	I <sub>C(ON)</sub>	0.5			mA		
On-State Collector Current L14G3	Ee = 0.5 mW/cm <sup>2</sup> , $V_{CE} = 5 V^{(7,8)}$	I <sub>C(ON)</sub>	2.0			mA		
Turn-On Time	$I_C = 2 \text{ mA}, V_{CC} = 10 \text{ V}, R_L = 100 \Omega$	t <sub>on</sub>		8		μs		
Turn-Off Time	$I_C = 2 \text{ mA}, V_{CC} = 10 \text{ V}, R_L = 100 \Omega$	t <sub>off</sub>		7		μs		
Saturation Voltage	$I_C = 1.0 \text{ mA}, Ee = 3.0 \text{ mW/cm}^{2(7,8)}$	V <sub>CE(SAT)</sub>	_		0.40	V		



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Figure 1. Light Current vs. Collector to Emitter Voltage

10

Ee = 20 mW/cm<sup>2</sup>

Ee = 10 mW/cm<sup>2</sup>

Ee = 10 mW/cm<sup>2</sup>

NORMALIZED TO:
Ee = 10 mW/cm<sup>2</sup>

VCE = 5 V

VCE = 5 V

VCE, COLLECTOR TO EMITTER VOLTAGE (V)

Figure 2. Light Current vs. Temperature

10

10

NORMALIZED TO:

V<sub>CE</sub> = 5 V

E<sub>e</sub> = 10 mW/cm<sup>2</sup>

E<sub>e</sub> - TOTAL IRRADIANCE IN mW/cm<sup>2</sup>

Figure 3. Normalized Light Current vs. Temperature

10

NORMALIZED TO:
VCE = 5 V

E<sub>e</sub> = 10 mW/cm<sup>2</sup>
T<sub>A</sub> = 25° C

0.1

-50

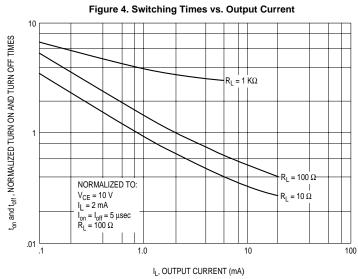
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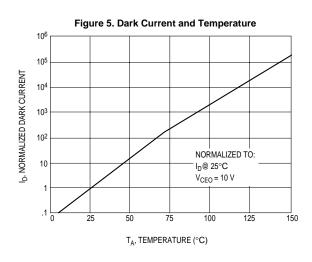
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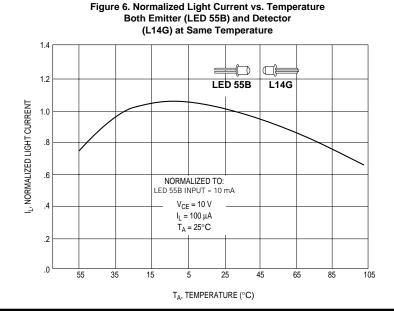
100

150

T<sub>A</sub>, TEMPERATURE (°C)









L14G1 L14G2 L14G3

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